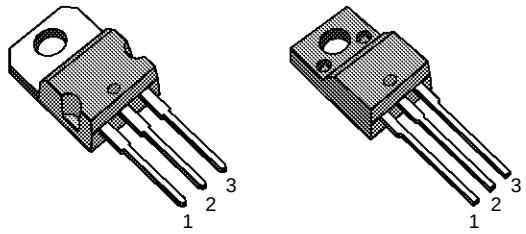
SGS-THOMSON MICROELECTRONICS

BUL57
BUL57PI

HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

- SGS-THOMSON PREFERRED SALESTYPES
- HIGH VOLTAGE CAPABILITY
- LOW SPREAD OF DYNAMIC PARAMETERS
- MINIMUM LOT-TO-LOT SPREAD FOR RELIABLE OPERATION
- VERY HIGH SWITCHING SPEED
- FULLY CHARACTERISED AT 125°C
- LARGE RBSOA
- U.L. RECOGNISED ISOWATT220 PACKAGE (U.L. FILE # E81734 (N)): ISOLATION VOLTAGE 1500V_{RMS}



TO-220 **ISOWATT220**

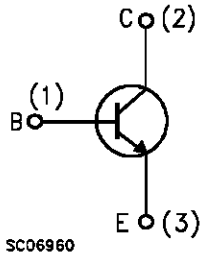
APPLICATIONS

- ELECTRONIC BALLASTS FOR FLUORESCENT LIGHTING
- SWITCH MODE POWER SUPPLIES

DESCRIPTION

The BUL57 and BUL57PI are manufactured using high voltage Multi Epitaxial Planar technology for high switching speeds and high voltage capability. They use a Cellular Emitter structure to enhance switching speeds.
The BUL series is designed for use in lighting applications and low cost switch-mode power supplies.

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		BUL57	BUL57PI	
V_{CES}	Collector-Emitter Voltage (V_{BE} = 0)	700		V
V_{CEO}	Collector-Emitter Voltage (I_B = 0)	400		V
V_{EBO}	Emitter-Base Voltage (I_C = 0)	9		V
I_C	Collector Current	7		A
I_{CM}	Collector Peak Current (t_p < 5 ms)	11		A
I_B	Base Current	4		A
I_{BM}	Base Peak Current (t_p < 5 ms)	7		A
P_{tot}	Total Dissipation at T_c = 25 °C	75	35	W
T_{stg}	Storage Temperature Range	-65 to 150		°C
T_j	Max. Operating Junction Temperature	150		°C

THERMAL DATA

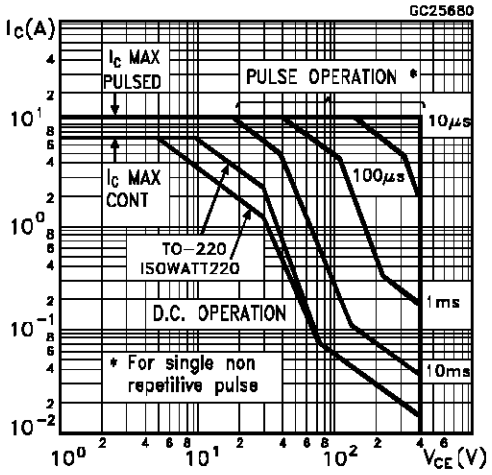
		TO-220	ISOWATT220	
$R_{thj\text{-}case}$	Thermal Resistance Junction-Case Max	1.65	3.58	°C/W
$R_{thj\text{-}amb}$	Thermal Resistance Junction-Ambient Max	62.5	62.5	°C/W

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

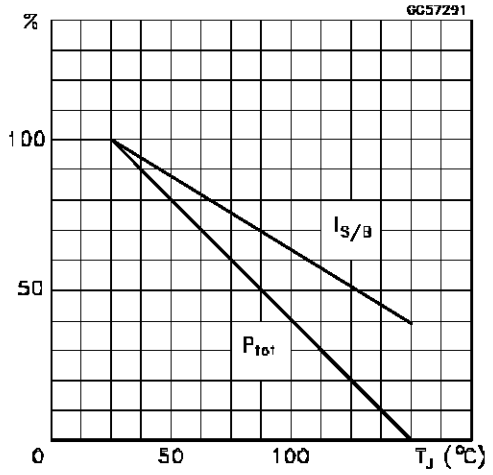
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CES}	Collector Cut-off Current (V_{BE} = 0)	V_{CE} = 700 V V_{CE} = 700 V T_j = 125 °C			100 500	µA µA
I_{CEO}	Collector Cut-off Current (I_B = 0)	V_{EC} = 400 V			250	µA
$V_{CEO(sus)}$	Collector-Emitter Sustaining Voltage	I_C = 100 mA L = 25 mH	400			V
V_{EBO}	Emitter-Base Voltage (I_C = 0)	I_E = 10 mA	9			V
$V_{CE(sat)}$*	Collector-Emitter Saturation Voltage	I_C = 2 A I_B = 0.4 A I_C = 3 A I_B = 0.6 A I_C = 4 A I_B = 0.8 A I_C = 5 A I_B = 1 A			0.65 0.75 1.2 2	V V V V
$V_{BE(sat)}$*	Base-Emitter Saturation Voltage	I_C = 2 A I_B = 0.4 A I_C = 5 A I_B = 1 A			1.2 1.6	V V
h_{FE}*	DC Current Gain	I_C = 2 A V_{CE} = 5 V I_C = 4 A V_{CE} = 5 V I_C = 10 mA V_{CE} = 5 V	15 6 8		40	
t_s t_f	INDUCTIVE LOAD Storage Time Fall Time	I_C = 3 A V_{CL} = 250 V I_{B1} = 0.6 A I_{B2} = -1.2 A L = 200 µH		1.8 60	2.6 110	µs ns
t_s t_f	INDUCTIVE LOAD Storage Time Fall Time	I_C = 3 A V_{CL} = 250 V I_{B1} = 0.6 A I_{B2} = -1.2 A L = 200 µH T_j = 125 °C		2.6 110		µs ns
t_s t_f	INDUCTIVE LOAD Storage Time Fall Time	I_C = 3 A I_{B1} = 0.6 A $V_{BE(off)}$ = -5 V R_{BB} = 0 Ω V_{CL} = 250 V L = 200 µH		1 54	1.6 100	µs ns
t_s t_f	INDUCTIVE LOAD Storage Time Fall Time	I_C = 3 A I_{B1} = 0.6 A $V_{BE(off)}$ = -5V R_{BB} = 0 Ω V_{CL} = 250 V L = 200 µH T_j = 125 °C		1.5 90		µs ns

* Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %

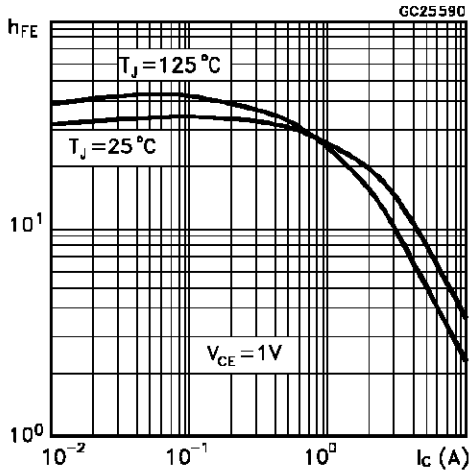
Safe Operating Areas



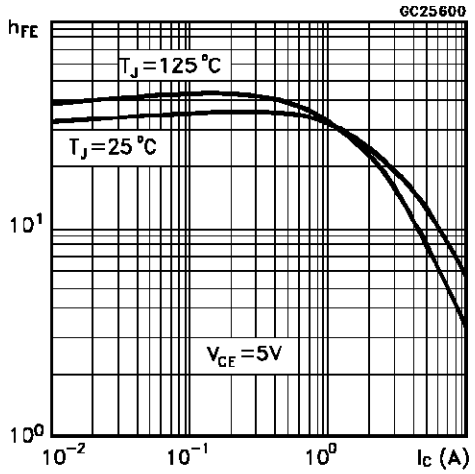
Derating Curves



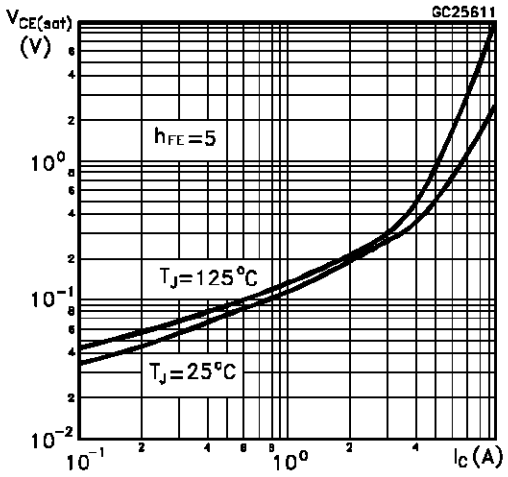
DC Current Gain



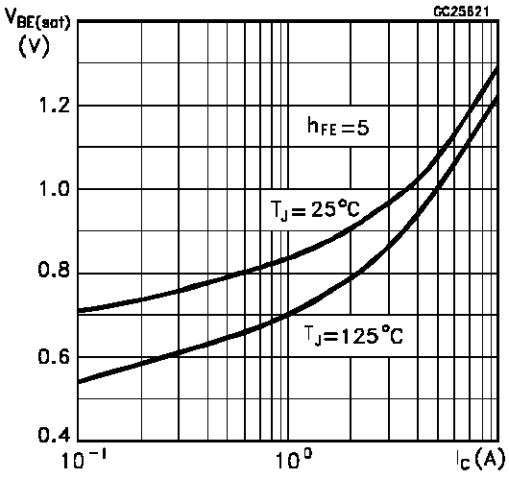
DC Current Gain



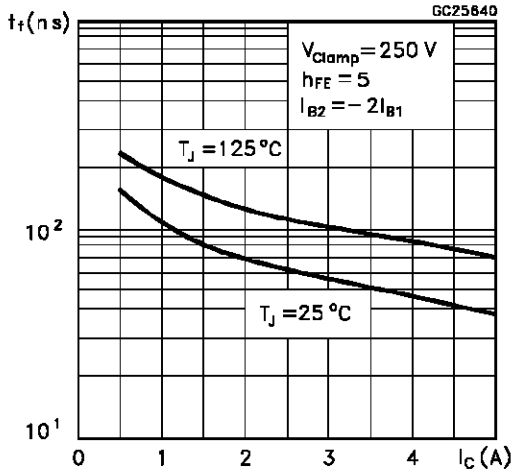
Collector Emitter Saturation Voltage



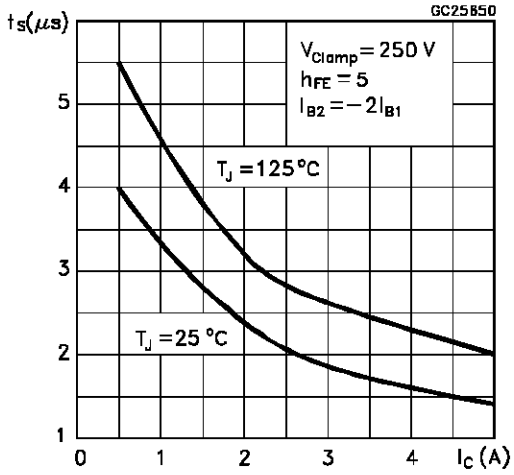
Base Emitter Saturation Voltage



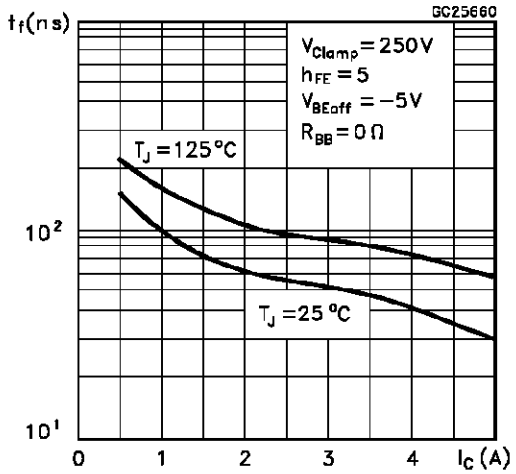
Inductive Fall Time



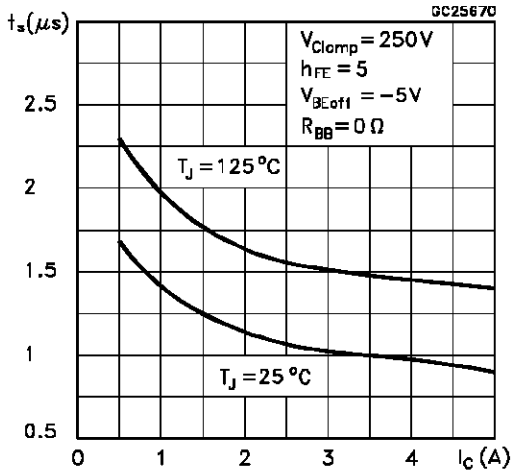
Inductive Storage Time



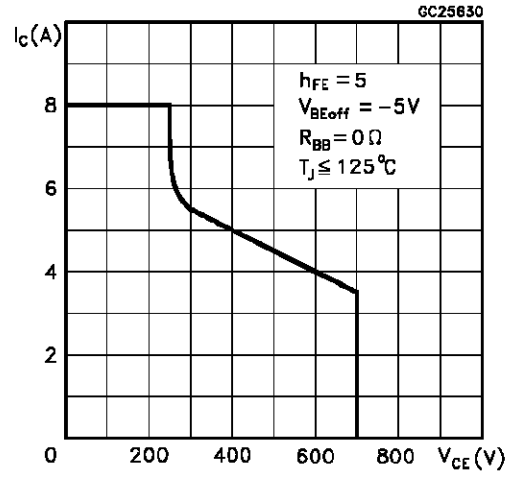
Inductive Fall Time



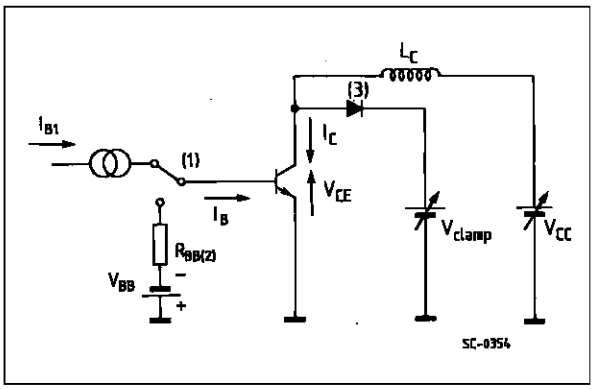
Inductive Storage Time



Reverse Biased SOA



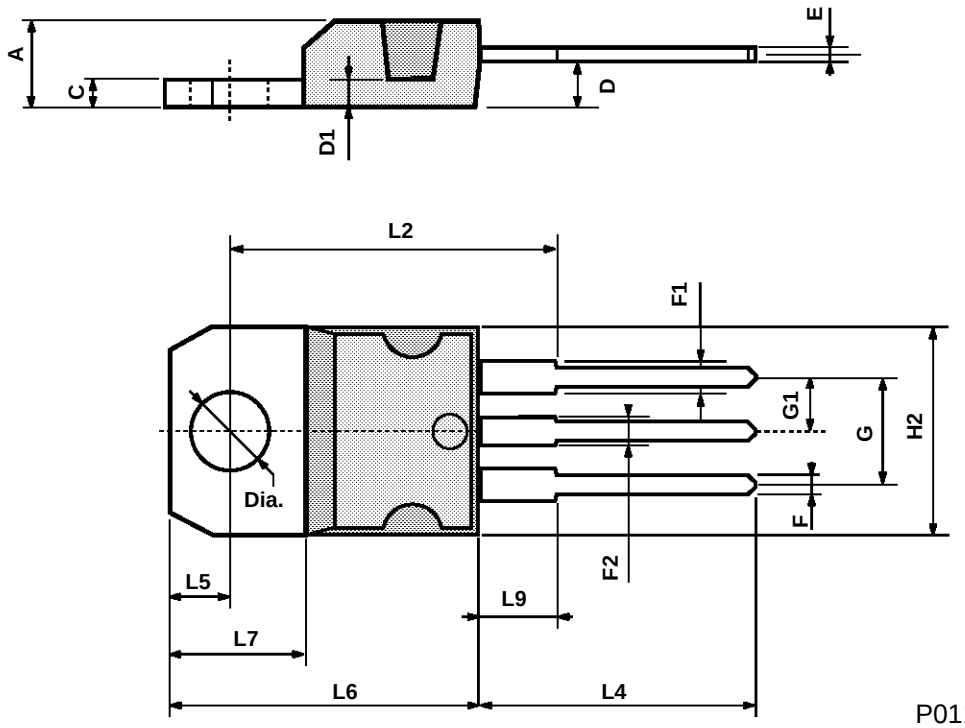
RBSOA and Inductive Load Switching Test Circuit



(1) Fast electronic switch
(2) Non-inductive Resistor
(3) Fast recovery rectifier

TO-220 MECHANICAL DATA

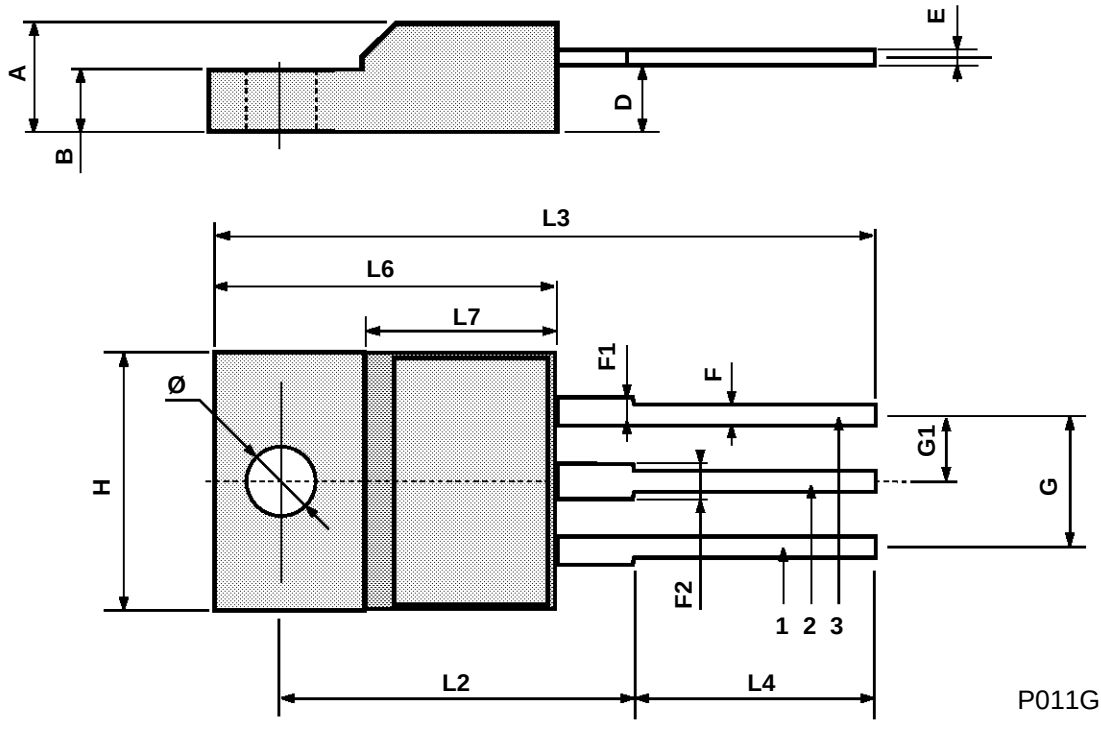
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



P011C

ISOWATT220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.4		0.7	0.015		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	0.385		0.417
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



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